

Supplemental Information:

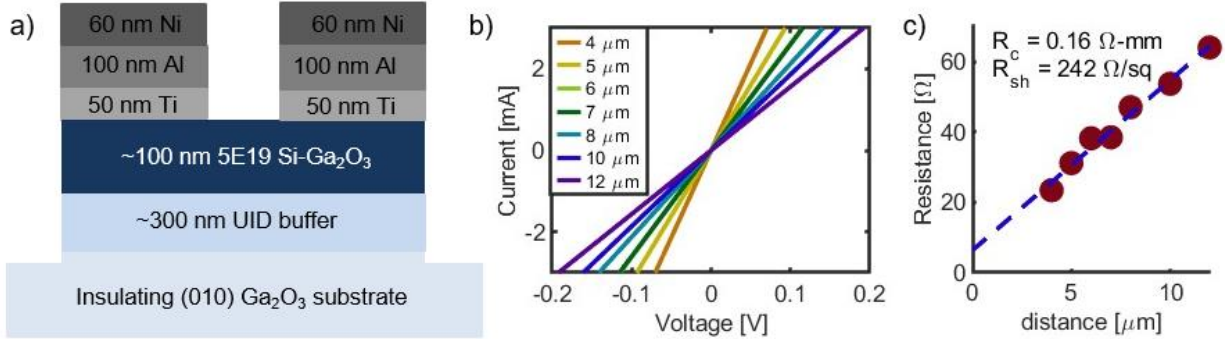


Figure 1: a) Layer structure of the implanted sample. b) IV measurements of alloyed contacts display linear, canonical ohmic behavior. c) TLM extraction of contact resistance gives R_c of $0.16 \Omega\text{-mm}$ and sheet resistance of $242 \Omega/\square$.

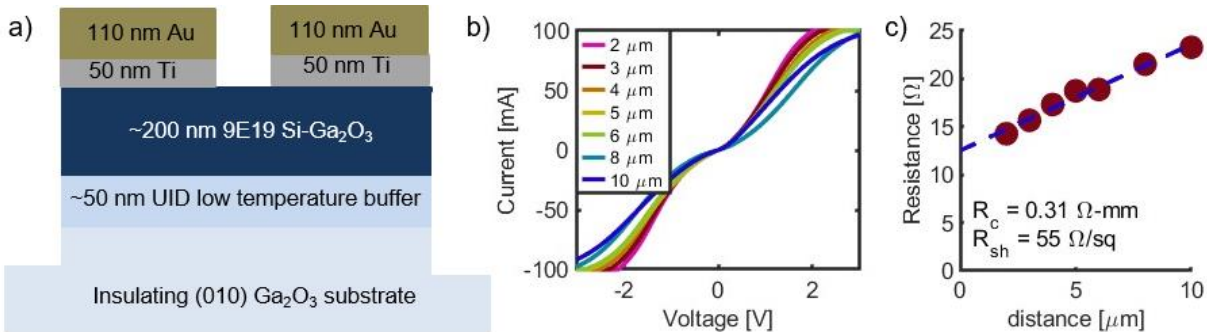


Figure 2: a) Layer structure of non-alloyed contacts to MOCVD grown n^+ Ga₂O₃. b) IV measurements display leaky-Schottky behavior. c) TLM extraction of R_c at 50 mA applied current. The extracted R_c is $0.31 \Omega\text{-mm}$, and the R_{sh} is $55 \Omega/\square$.

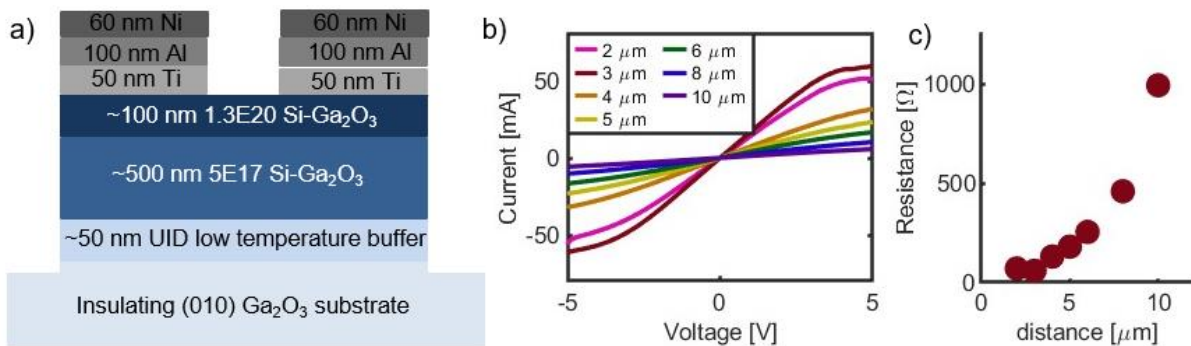


Figure 3: a) Layer structure of alloyed contacts to MOCVD grown n^+ on n^- Ga₂O₃. b) IV measurements show canonical ohmic behavior with current saturation due to thermal effects and source choke. c) Spatially non-uniform contacts make extraction of R_c by TLM methods impossible.

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